

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFSL4610

D(2)

FEATURES

- · Static drain-source on-resistance: RDs(on) ≤13.5mΩ
- · Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

SYMBOL

VDSS

 V_{GS}

ΙD

IDM

 \mathbf{P}_{D}

Ti

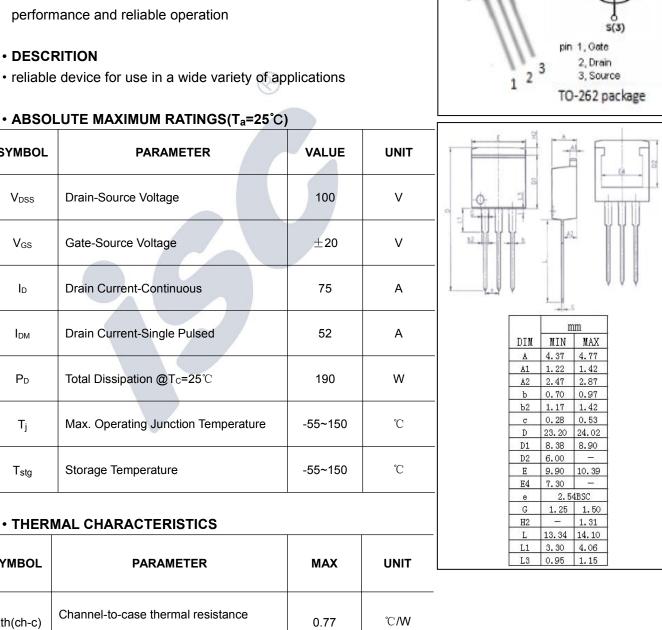
Tstg

SYMBOL

Rth(ch-c)

· reliable device for use in a wide variety of applications





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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	100			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =100 μ A	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =44A			14	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V			±200	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V; V _{GS} = 0V			20	μA
V _{SD}	Diode forward voltage	IS= 44A, V _{GS} = 0V			1.3	V



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